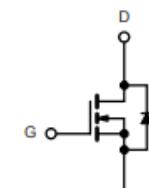
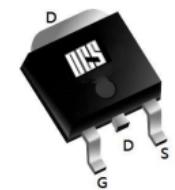


## Features

- Split gate trench Technology
- Supper high density cell design
- Fast Switching Extremely Low Threshold Voltage
- 100% Avalanche test
- Pb-free lead plating, RoHS compliant
- Package TO252-2L

T0252



N-Channel MOSFET

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(on)</sub> Type	I <sub>D</sub>
100V	65m Ω @ V <sub>GS</sub> =10V	15A
	85m Ω @ V <sub>GS</sub> =5.0V	

## Application

- DC/DC converters
- Power supply converters circuit
- Power Load Switch



## Absolute Maximum Ratings (T<sub>A</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current <sup>1,5</sup>	I <sub>D</sub>	15	A
		10	
Pulsed Drain Current <sup>2,5</sup>	I <sub>DM</sub>	55	A
Single Pulse Avalanche Energy <sup>3</sup>	EAS	16	mJ
Total Power Dissipation <sup>4</sup>	PD	30	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 To 150	°C

## Thermal Characteristic (T<sub>A</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient <sup>1</sup>	R <sub>θJA</sub>	62	°C/W
Thermal Resistance, Junction-Case <sup>1</sup>	R <sub>θJC</sub>	2.2	°C/W